

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Fumitaka ARAI, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE INCLUDING IMPROVED GATE ELECTRODE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment form is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.



22850

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Respectfully submitted,

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DOCKET NO.: 241987US2S

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SERIAL NO: New Application

FILED: HEREWITH

FOR: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE INCLUDING  
IMPROVED GATE ELECTRODE

**STATEMENT OF RELEVANCY**

**Reference AO on Form PTO-1449:**

This publication is referred to in the specification. See page 5, line 24.

**Reference AP on Form PTO-1449:**

This publication is referred to in the specification. See page 6, line 2.

**Reference AQ on Form PTO-1449:**

This publication is referred to in the specification. See page 6, line 8.

**Reference AW on Form PTO-1449:**

This publication is referred to in the specification. See page 6, line 11.

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

241987US2S

SERIAL NO.

New Application

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Fumitaka ARAI, et al.

FILING DATE

Herewith

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	11-145429	05/28/99	Japan		X
	AP	2002-217318	08/02/02	Japan		X
	AQ	2002-50703	02/15/02	Japan		X
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	Y. Sasago, et al., "10 MB/s Mult-Level programming of Gb-Scale Flash Memory Enabled by New AG-AND Cell Technology", 2002 IEEE, pgs.952 -954 IEDM, 21.6.1
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.